



## **TSM35N03PQ56**

## 30V N-Channel Power MOSFET

#### PDFN 5x6

# 8

#### Pin Definition:

1. Source	8. Drair
2. Source	7. Drair
3. Source	6. Drair
4. Gate	5. Drair

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
00	7 @ V <sub>GS</sub> =10V	12
30	9 @ V <sub>GS</sub> =4.5V	10

#### **Features**

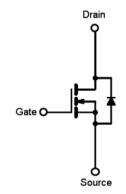
- Advanced Trench Technology
- Low On-Resistance
- Low gate charge typical @ 8.2nC (Typ.)
- Low Crss typical @ 90pF (Typ.)

#### **Ordering Information**

Part No.	Package	Packing
TSM35N03PQ56 RLG	PDFN56	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

#### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Ratings** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage	Gate-Source Voltage		±25	<b>V</b>	
Continuous Drain Current	T <sub>C</sub> =25°C		35		
	T <sub>C</sub> =70°C		35	Α	
	T <sub>A</sub> =25°C	I <sub>D</sub>	22		
	T <sub>A</sub> =70°C		18		
Drain Current-Pulsed Note 1		I <sub>DM</sub>	60	Α	
Avalanche Current, L=0.5mH		I <sub>AS</sub> , I <sub>AR</sub>	26	Α	
Avalanche Energy, L=0.5mH		E <sub>AS</sub> , E <sub>AR</sub>	33	mJ	
Maximum Power Dissipation	T <sub>C</sub> =25°C		35		
	T <sub>C</sub> =70°C		23	W	
	T <sub>A</sub> =25°C	P <sub>D</sub>	4.2		
	T <sub>A</sub> =70°C		2.7		
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

<sup>\*</sup> Limited by maximum junction temperature

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ <sub>JC</sub>	3.5	°C/W
Thermal Resistance - Junction to Ambient	RO <sub>JA</sub>	30	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



## **TSM35N03PQ56**

### 30V N-Channel Power MOSFET



#### **Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		-		•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Drain-Source On-State Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A	Б		5.5	7	mΩ
	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	R <sub>DS(ON)</sub>		7.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.3		2.5	V
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	I <sub>DSS</sub>			1	μA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic						
Total Gate Charge		$Q_g$		8.2		nC
Gate-Source Charge	$V_{DS} = 15V, I_D = 16A,$	$Q_{gs}$		2.7		
Gate-Drain Charge	$V_{GS} = 4.5V$	$Q_{gd}$		2.2		
Input Capacitance	45)/ )/ 0)/	C <sub>iss</sub>		1050		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		210		pF
Reverse Transfer Capacitance		$C_{rss}$		90		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>	I	9		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$	t <sub>r</sub>	I	9		
Turn-Off Delay Time	$R_G = 1\Omega$	$t_{d(off)}$	I	20		ns
Turn-Off Fall Time		t <sub>f</sub>	I	7		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =2.3A	$V_{SD}$		0.75	1.3	٧
Reverse Recovery Time	I <sub>S</sub> = 3.2A, T <sub>J</sub> =25 °C	t <sub>fr</sub>		22		ns
Reverse Recovery Charge Notes:	dl/dt = 100A/µs	Q <sub>fr</sub>		14		nC

#### Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2.  $R\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R\theta_{JC}$  is guaranteed by design while  $R\theta_{CA}$  is determined by the user's board design.  $R\theta_{JA}$  shown below for single device operation on FR-4 in still air
- 3. The maximum current rating is limited by package.

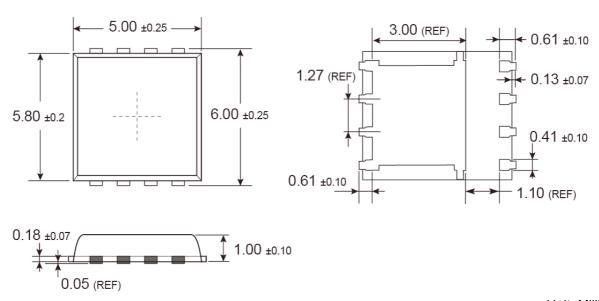


## **TSM35N03PQ56**

## 30V N-Channel Power MOSFET



## **PDFN56 Mechanical Drawing**



Unit: Millimeters



## TSM35N03PQ56 30V N-Channel Power MOSFET

#### **Notice**

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.